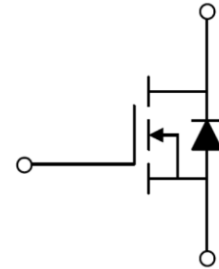


PowerMOSFET Wafer Datasheet

FEATURES

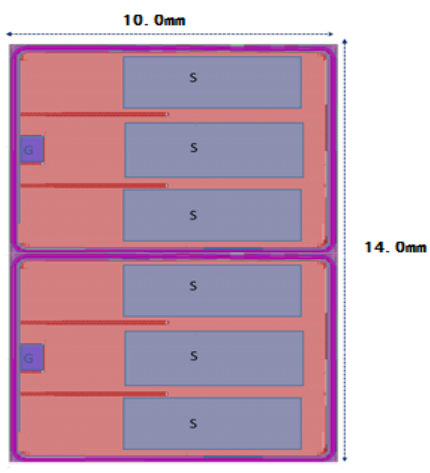
- 500V、100A* , N-channel
- $R_{DS(on)}=46m\Omega(MAX)$
- Ultra low Q_{gd}
- Fast switching
- 100% CP tested



Electrical Characteristics(T_J=25°C)

Parameter	Description	Min.	Typ.	Max.	Unit	Test Condition
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	500			V	$V_{GS}=0V, I_D=250\mu A$
$R_{DS(on)}$	Static Drain-Source On-Resistance		40	46	m Ω	$V_{GS}=10V, I_D=50A$
$V_{GS(th)}$	Gate Threshold Voltage	2.0		4.0	V	$V_{DS}=V_{GS}, I_D=250\mu A$
I_{DSS}	Drain-to-Source Leakage Current			1	μA	$V_{DS}=500V, V_{GS}=0V, T_J=25^\circ C$
I_{GSS}	Gate-Body Leakage Current			± 100	nA	$V_{GS}=\pm 30V$
V_{SD}	Body Diode Voltage			1.4	V	$V_{GS}=0V, I_{SD}=100A$
T_J, T_{stg}	Operating and Storage Temperature Range	-55~+150			$^\circ C$	

Mechanical Data

Die Size	14000×10000	μm^2	
Gate Pad Size	500×1000*8		
Source Pad Size	2010×6000*6		
Scribe Line Size	60	μm	
Wafer Diameter	150	mm	
Wafer Thickness	280	μm	
Passivation Frontside	SIN	---	
Source Metallization	AL	4.0	
Drain Metallization	Ti- Ni - Ag	1.3	
Reject Ink Dot Size	0.51	mm	
Recommended Storage Environment	Store in original container, in dessicated nitrogen, with no contamination		

* Electrical characteristics are reported for the reference packaged part (TO-264\SOT-227B) and can not be guaranteed in die sales form.

Variations in customer packaging materials, dimensions and processes may affect parametric performance.